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### Claim Status

Claims 1-20 (canceled).

Claim 21-27 (canceled)

Claim 28 (previously presented): A programming metallization cell memory (PMCm) comprising:

- a. a pair of electrodes; and
- b. a thin metal layer; and
- c. a single resistive layer with a plurality of ultra-small solid electrolyte resistive element, or
- d. a lamination of said resistive layer, thin metal layer and conductive layer.

Claim 29 (previously presented): The top surface and bottom surface of the said solid electrolyte resistive elements in the claim 28 contact directly with the adjacent metal layer and bottom electrode, respectively.

Claim 30 (previously presented): The device of claim 28 with lamination of resistive layer, thin metal layer and conductive layer wherein the top surface and bottom surface of said solid electrolyte element contact with adjacent said conductor layer and thin metal layer.

Claim 31 (previously presented): The device of claim 28 wherein the size of the solid electrolyte resistive element is in the range of about 1.0-100 nm in diameter.